

## Features

- Advanced Shield Gate Trench technology
- Super Low Gate Charge
- High-Speed Switching
- 100% EAS Guaranteed
- Green Device Available

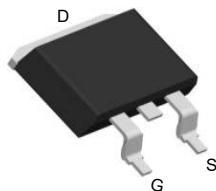
## Product Summary



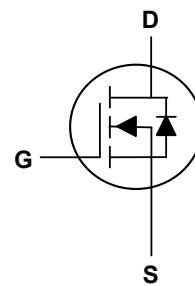
$V_{DS}$	100	V
$I_D$	150	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	3.5	mΩ

## Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



TO-263 Top View



## Absolute Maximum Ratings( $T_c=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$I_D$	150	A
Continuous Drain Current <sup>1</sup>	$I_D$	108	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	550	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	756	mJ
Total Power Dissipation <sup>4</sup>	$P_D$	188	W
Storage Temperature Range	$T_{STG}$	-55 to 150	°C
Operating Junction Temperature Range	$T_J$	-55 to 150	°C

## Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	55	°C/W
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	0.8	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	100	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=20\text{A}$	---	3.5	4.2	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D = 250\mu\text{A}$	2.0	2.8	4.0	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=100\text{V}$ , $V_{\text{GS}}=0\text{V}$	---	---	1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	$\text{nA}$
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=5\text{V}$ , $I_D=20\text{A}$	55	---	---	S
Total Gate Charge	$Q_g$	$V_{\text{DS}}=40\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=10\text{A}$	---	57	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	11	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	16	---	
Turn-On Delay Time	$T_{\text{d}(\text{on})}$	$V_{\text{DD}}=50\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=6\Omega$ , $I_D=1\text{A}$	---	14	---	ns
Rise Time	$T_r$		---	34	---	
Turn-Off Delay Time	$T_{\text{d}(\text{off})}$		---	60	---	
Fall Time	$T_f$		---	50	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	3430	---	pF
Output Capacitance	$C_{\text{oss}}$		---	900	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	13	---	

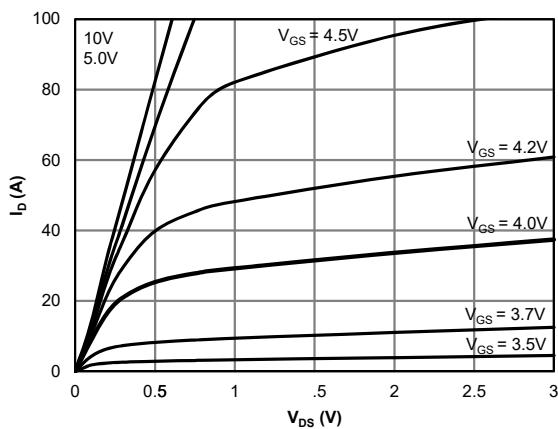
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_S=1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.2	V

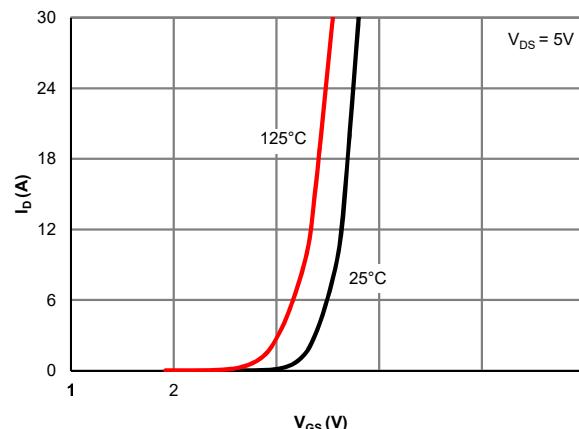
**Note:**

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=25\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $L=0.5\text{mH}$
4. The power dissipation is limited by  $150^\circ\text{C}$  junction temperature

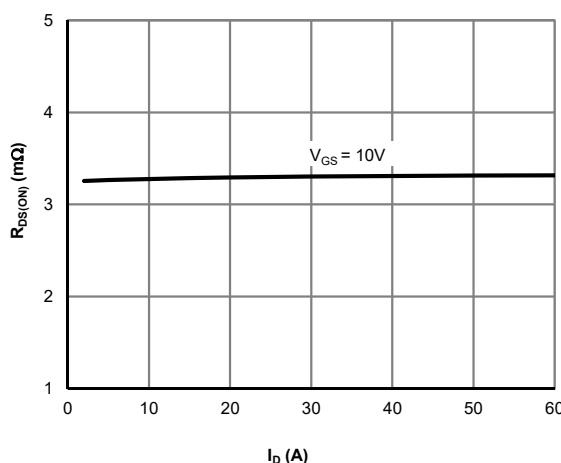
## Typical Characteristics



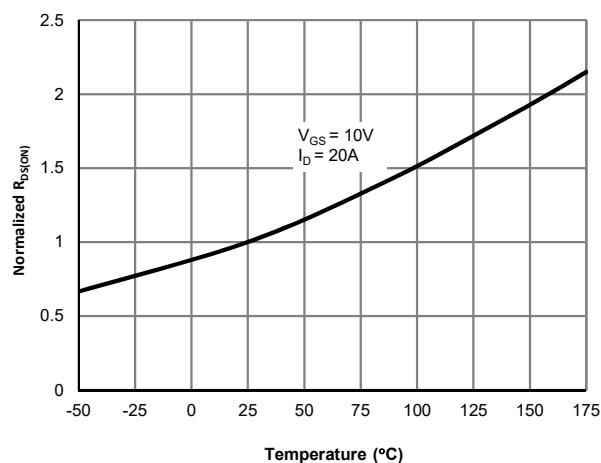
**Figure 1: Saturation Characteristics**



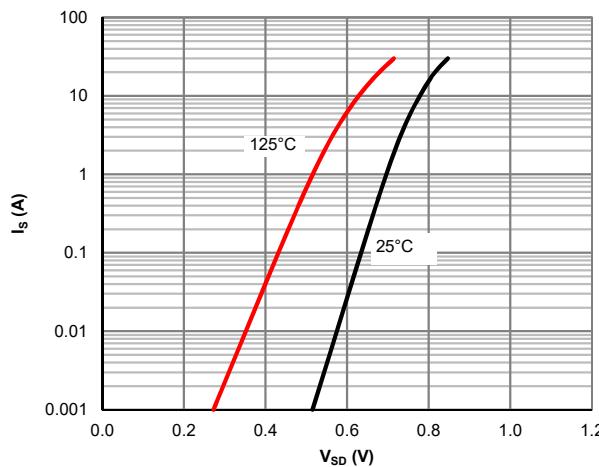
**Figure 2: Transfer Characteristics**



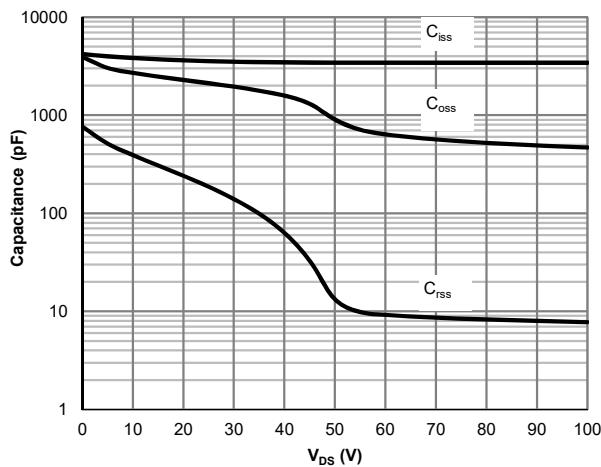
**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**



**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**



**Figure 5: Body-Diode Characteristics**



**Figure 6: Capacitance Characteristics**

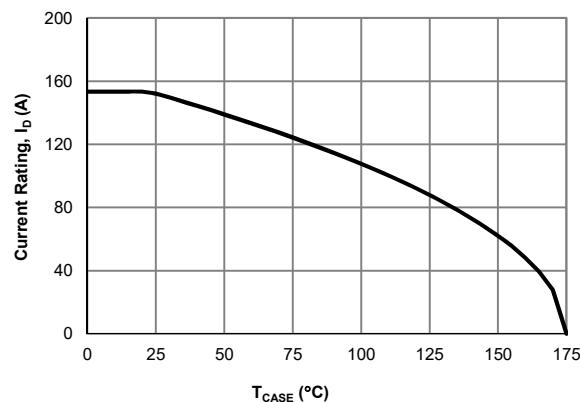


Figure 7: Current De-rating

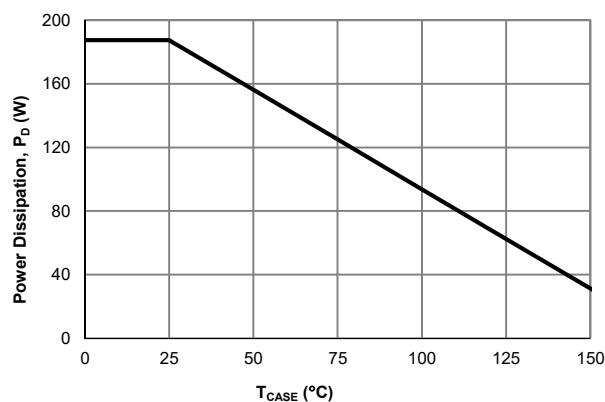


Figure 8: Power De-rating

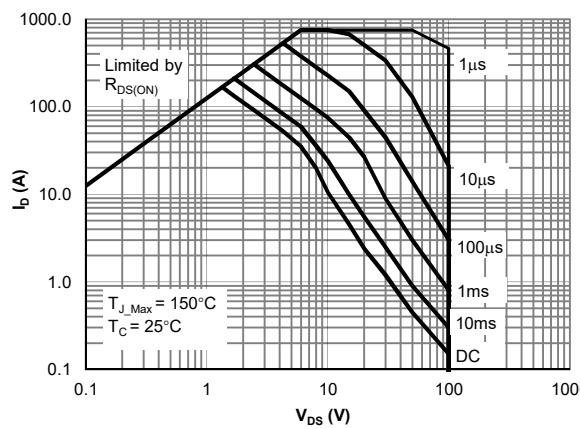


Figure 9: Maximum Safe Operating Area

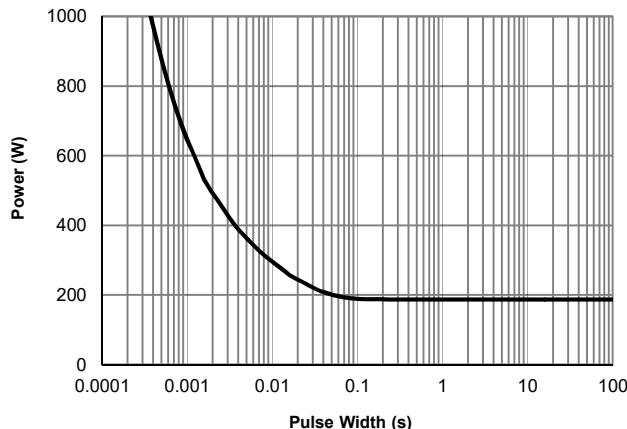


Figure 10: Single Pulse Power Rating, Junction-to-Case

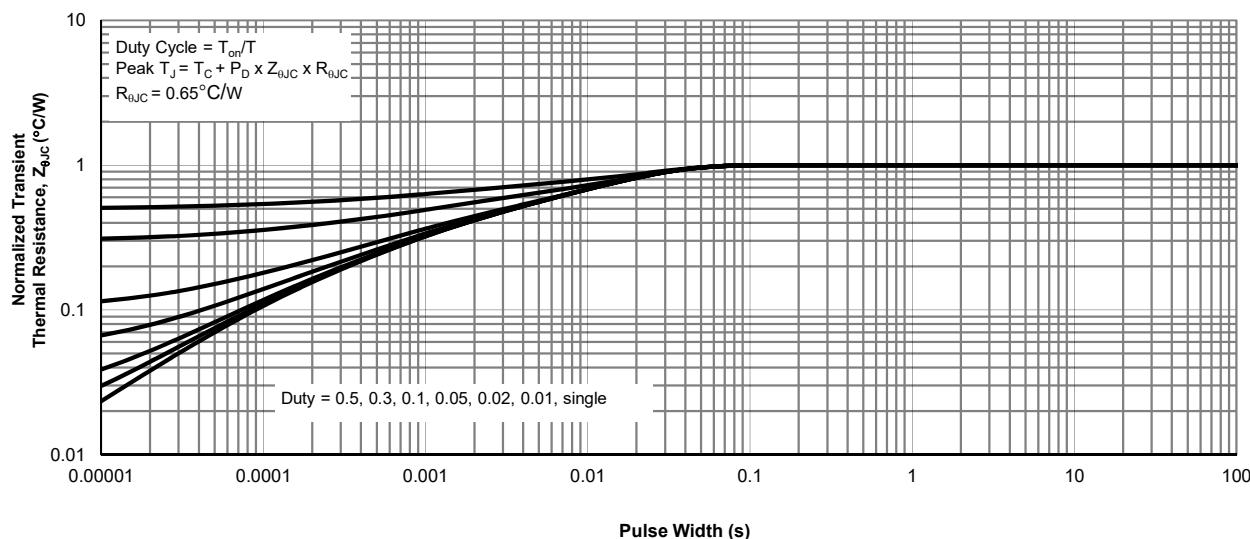
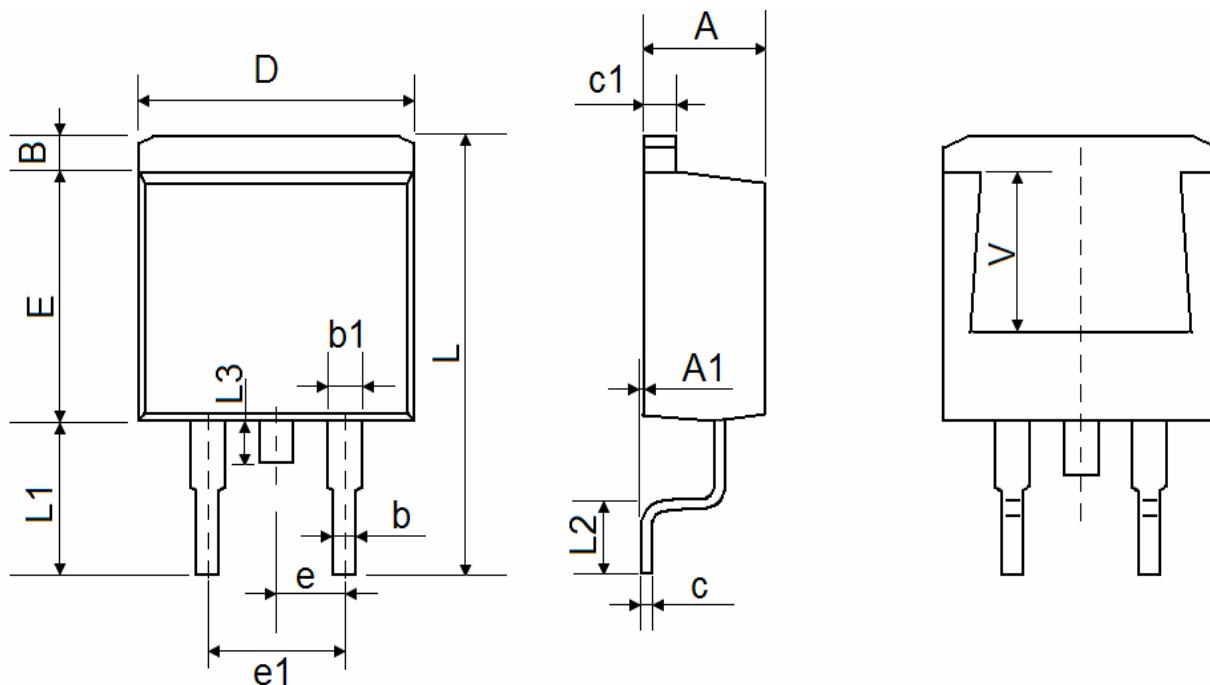


Figure 11: Normalized Maximum Transient Thermal Impedance

### TO-263 Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	4.40	4.55	4.70	<b>A1</b>	0.00	0.07	0.15
<b>B</b>	1.00	1.20	1.40	<b>b</b>	0.65	0.80	0.95
<b>b1</b>	1.10	1.15	1.37	<b>c</b>	0.30	0.40	0.53
<b>c1</b>	1.10	1.25	1.37	<b>D</b>	9.80	10.00	10.40
<b>E</b>	8.50	8.80	9.20	<b>e</b>	2.54 REF		
<b>e1</b>	4.90	5.10	5.40	<b>L</b>	14.80	15.20	15.70
<b>L1</b>	5.00	5.25	5.60	<b>L2</b>	2.05	2.45	2.80
<b>L3</b>	1.20	1.50	1.80	<b>V</b>	5.60 REF		